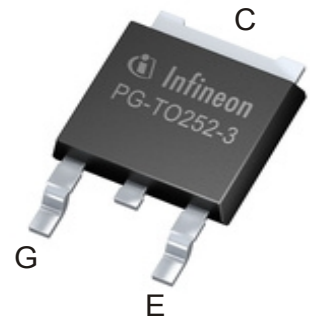
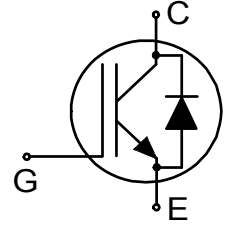


## TRENCHSTOP™ IGBT6

IGBT in trench and field-stop technology with soft, fast recovery anti-parallel Rapid diode

### Features and Benefits:

- Very low  $V_{CE(sat)}$  1.5V (typ.)
  - Maximum junction temperature 175°C
  - Short circuit withstand time 3μs
- Trench and field-stop technology for 650V applications offers :
- very tight parameter distribution
  - high ruggedness, temperature stable behavior
  - low  $V_{CEsat}$  and positive temperature coefficient
- Low gate charge  $Q_G$
  - Pb-free lead plating; RoHS compliant
  - Very soft, fast recovery anti-parallel Rapid diode
  - Complete product spectrum and PLECS Models:  
[www.infineon.com/igbt](http://www.infineon.com/igbt)



### Potential Applications:

- Drives
- GPD (general purpose drives)
- Major home appliances
- Air conditioning
  - Other major home appliances
- Small home appliances
- Other small home appliances

### Product Validation:

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

### Key Performance and Package Parameters

Type	$V_{CE}$	$I_C$	$V_{CEsat}, T_{vj}=25^{\circ}C$	$T_{vjmax}$	Marking	Package
IKD06N65ET6	650V	6A	1.5V	175°C	K06EET6	PG-TO252-3

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